

MOSFET - Power, Single N-Channel

80 V, 3.3 mΩ, 132 A



ON Semiconductor®

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NVMYS003N08LH

Features

- Small Footprint (5x6 mm) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- LFPACK4 Package, Industry Standard
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

| Parameter | Symbol | Value | Unit | |
|-----------------------------------------------------------------------------|------------------------------------------------|---------------------------|------------------|---|
| Drain-to-Source Voltage | V_{DSS} | 80 | V | |
| Gate-to-Source Voltage | V_{GS} | ± 20 | V | |
| Continuous Drain Current $R_{\theta JC}$ (Notes 1, 3) | Steady State | $T_C = 25^\circ\text{C}$ | I_D 132 | A |
| | | $T_C = 100^\circ\text{C}$ | 93 | |
| Power Dissipation $R_{\theta JC}$ (Note 1) | Steady State | $T_C = 25^\circ\text{C}$ | P_D 137 | W |
| | | $T_C = 100^\circ\text{C}$ | 68 | |
| Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2, 3) | Steady State | $T_A = 25^\circ\text{C}$ | I_D 22 | A |
| | | $T_A = 100^\circ\text{C}$ | 16 | |
| Power Dissipation $R_{\theta JA}$ (Notes 1, 2) | Steady State | $T_A = 25^\circ\text{C}$ | P_D 3.8 | W |
| | | $T_A = 100^\circ\text{C}$ | 1.9 | |
| Pulsed Drain Current | $T_A = 25^\circ\text{C}, t_p = 10 \mu\text{s}$ | I_{DM} 900 | A | |
| Operating Junction and Storage Temperature Range | T_J, T_{stg} | -55 to +175 | $^\circ\text{C}$ | |
| Source Current (Body Diode) | I_S | 114 | A | |
| Single Pulse Drain-to-Source Avalanche Energy ($I_{L(pk)} = 9 \text{ A}$) | E_{AS} | 1211 | mJ | |
| Lead Temperature for Soldering Purposes (1/8" from case for 10 s) | T_L | 260 | $^\circ\text{C}$ | |

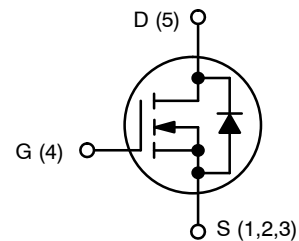
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

| Parameter | Symbol | Value | Unit |
|---------------------------------------------|-----------------|-------|---------------------------|
| Junction-to-Case - Steady State | $R_{\theta JC}$ | 1.1 | $^\circ\text{C}/\text{W}$ |
| Junction-to-Ambient - Steady State (Note 2) | $R_{\theta JA}$ | 39.6 | |

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using a 650 mm², 2 oz. Cu pad.
3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

| $V_{(BR)DSS}$ | $R_{DS(ON) MAX}$ | $I_D MAX$ |
|---------------|------------------|-----------|
| 80 V | 3.3 mΩ @ 10 V | 132 A |
| | 4.3 mΩ @ 4.5 V | |

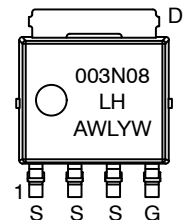


N-CHANNEL MOSFET



LFPACK4 CASE 760AB

MARKING DIAGRAM



003N08LH = Specific Device Code
 A = Assembly Location
 WL = Wafer Lot
 Y = Year
 W = Work Week

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

NVMYS003N08LH

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

| Parameter | Symbol | Test Condition | Min | Typ | Max | Unit |
|-----------|--------|----------------|-----|-----|-----|------|
|-----------|--------|----------------|-----|-----|-----|------|

OFF CHARACTERISTICS

| | | | | | | |
|-----------------------------------------------------------|--------------------------------------|--------------------------------------------------|------------------------|------|-----|-------|
| Drain-to-Source Breakdown Voltage | V _{(BR)DSS} | V _{GS} = 0 V, I _D = 250 μA | 80 | | | V |
| Drain-to-Source Breakdown Voltage Temperature Coefficient | V _{(BR)DSS} /T _J | | | 40.7 | | mV/°C |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{GS} = 0 V, V _{DS} = 80 V | T _J = 25°C | | 10 | μA |
| | | | T _J = 125°C | | 100 | |
| Gate-to-Source Leakage Current | I _{GSS} | V _{DS} = 0 V, V _{GS} = 20 V | | | 100 | nA |

ON CHARACTERISTICS (Note 4)

| | | | | | | | |
|-----------------------------------|-------------------------------------|-------------------------------------------------------------|-----------------------|------|-----|-------|----|
| Gate Threshold Voltage | V _{GS(TH)} | V _{GS} = V _{DS} , I _D = 183 μA | 1.2 | | 2.0 | V | |
| Threshold Temperature Coefficient | V _{GS(TH)} /T _J | | | -4.4 | | mV/°C | |
| Drain-to-Source On Resistance | R _{DS(on)} | V _{GS} = 10 V | I _D = 50 A | | 2.7 | 3.3 | mΩ |
| | | V _{GS} = 4.5 V | I _D = 50 A | | 3.4 | 4.3 | |
| Forward Transconductance | g _{FS} | V _{DS} = 8 V, I _D = 50 A | | 240 | | S | |

CHARGES, CAPACITANCES & GATE RESISTANCE

| | | | | | | |
|------------------------------|---------------------|------------------------------------------------------------------------|--|------|--|----|
| Input Capacitance | C _{ISS} | V _{GS} = 0 V, f = 1 MHz, V _{DS} = 40 V | | 3735 | | pF |
| Output Capacitance | C _{OSS} | | | 458 | | |
| Reverse Transfer Capacitance | C _{RSS} | | | 19 | | |
| Total Gate Charge | Q _{G(TOT)} | V _{GS} = 10 V, V _{DS} = 40 V; I _D = 50 A | | 64 | | nC |
| Total Gate Charge | Q _{G(TOT)} | V _{GS} = 4.5 V, V _{DS} = 40 V; I _D = 50 A | | 31 | | nC |
| Threshold Gate Charge | Q _{G(TH)} | | | 6.3 | | |
| Gate-to-Source Charge | Q _{GS} | | | 11.1 | | |
| Gate-to-Drain Charge | Q _{GD} | | | 10.5 | | |
| Plateau Voltage | V _{GP} | | | 3.0 | | |

SWITCHING CHARACTERISTICS (Note 5)

| | | | | | | |
|---------------------|---------------------|---------------------------------------------------------------------------------------------------|--|-----|--|----|
| Turn-On Delay Time | t _{d(ON)} | V _{GS} = 4.5 V, V _{DS} = 64 V, I _D = 50 A, R _G = 2.5 Ω | | 20 | | ns |
| Rise Time | t _r | | | 122 | | |
| Turn-Off Delay Time | t _{d(OFF)} | | | 42 | | |
| Fall Time | t _f | | | 21 | | |

DRAIN-SOURCE DIODE CHARACTERISTICS

| | | | | | | | |
|-------------------------|-----------------|---------------------------------------------------------------------------------|------------------------|----|------|-----|----|
| Forward Diode Voltage | V _{SD} | V _{GS} = 0 V, I _S = 50 A | T _J = 25°C | | 0.79 | 1.2 | V |
| | | | T _J = 125°C | | 0.71 | | |
| Reverse Recovery Time | t _{RR} | V _{GS} = 0 V, dI _S /dt = 100 A/μs, I _S = 50 A | | 57 | | ns | |
| Charge Time | t _a | | | 31 | | | |
| Discharge Time | t _b | | | 27 | | | |
| Reverse Recovery Charge | Q _{RR} | | | 66 | | | nC |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
- Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

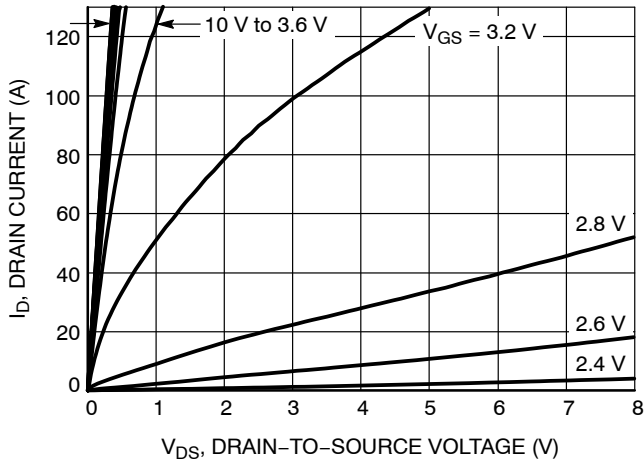


Figure 1. On-Region Characteristics

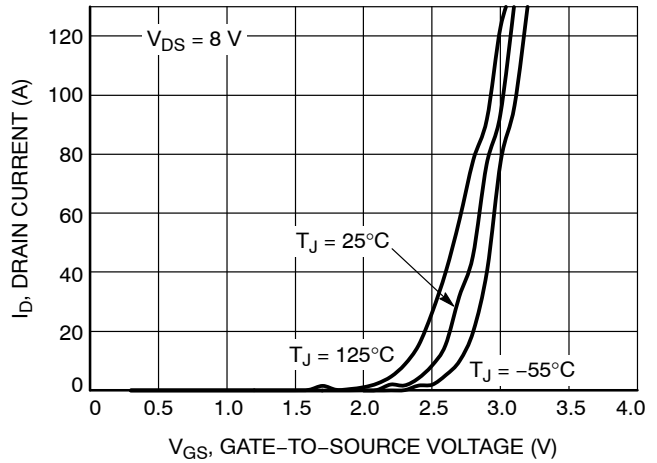


Figure 2. Transfer Characteristics

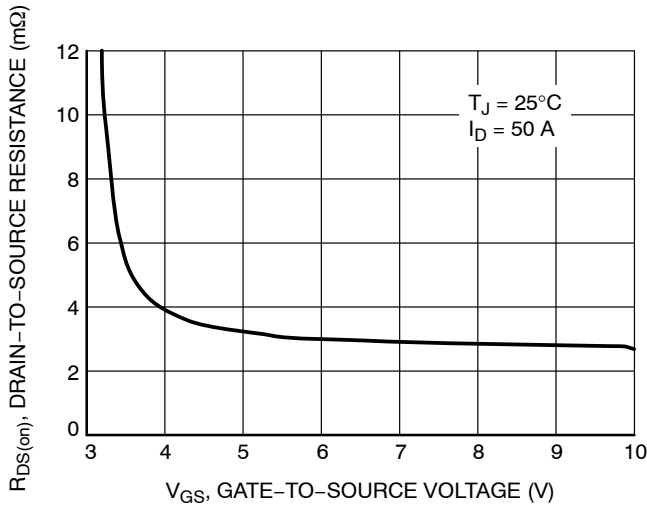


Figure 3. On-Resistance vs. Gate-to-Source Voltage

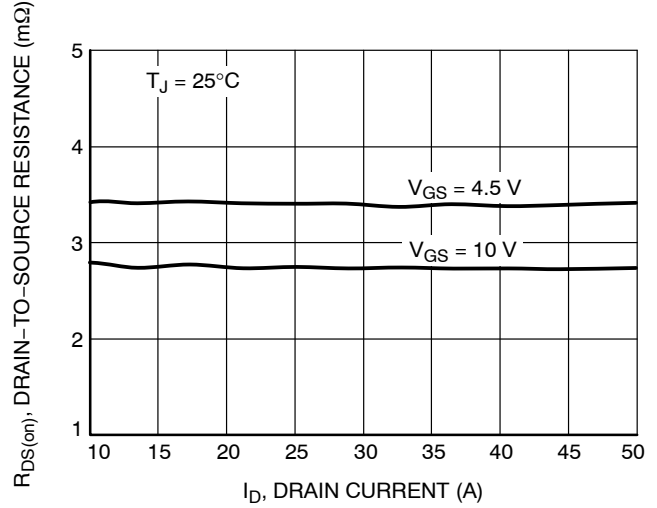


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

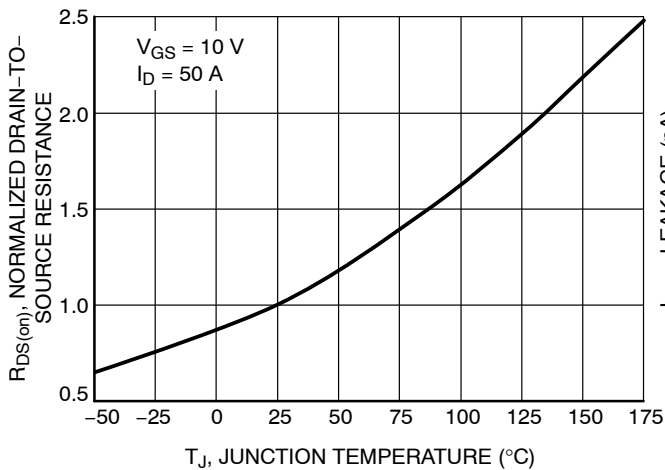


Figure 5. On-Resistance Variation with Temperature

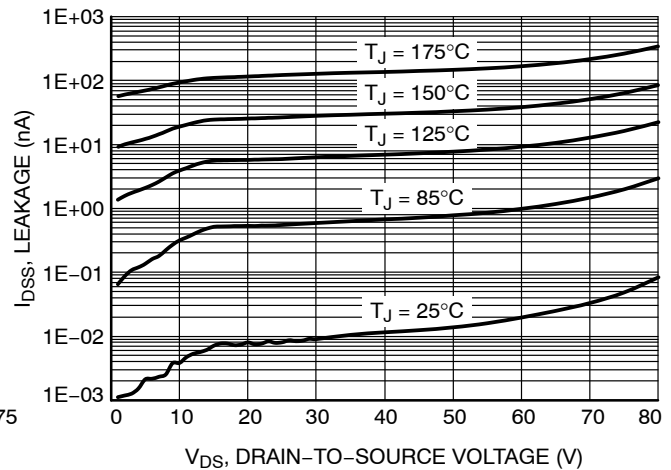


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

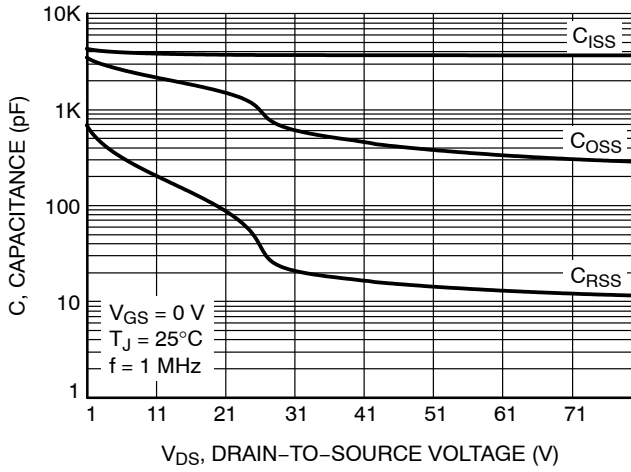


Figure 7. Capacitance Variation

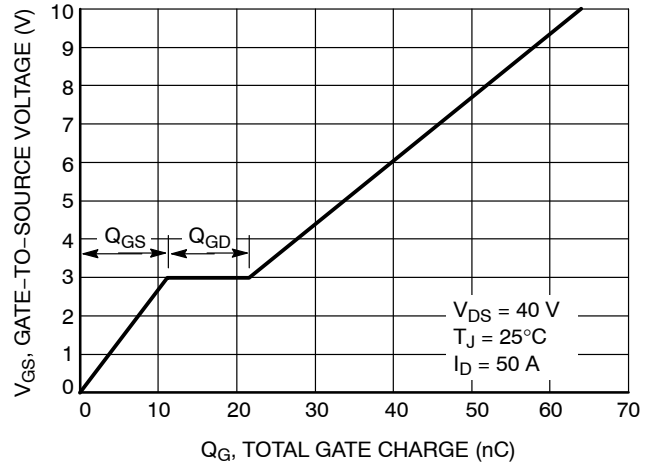


Figure 8. Gate-to-Source vs. Total Charge

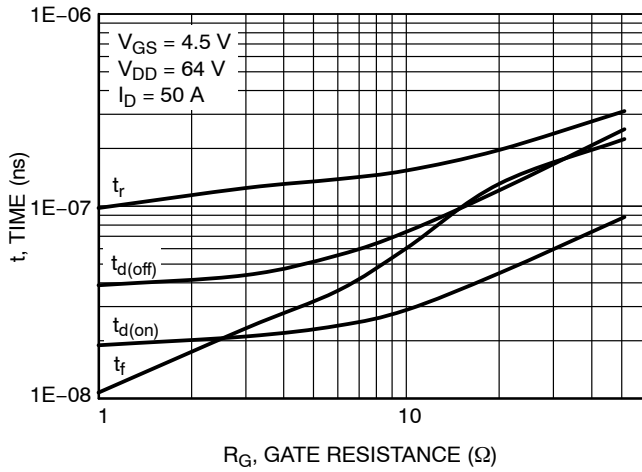


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

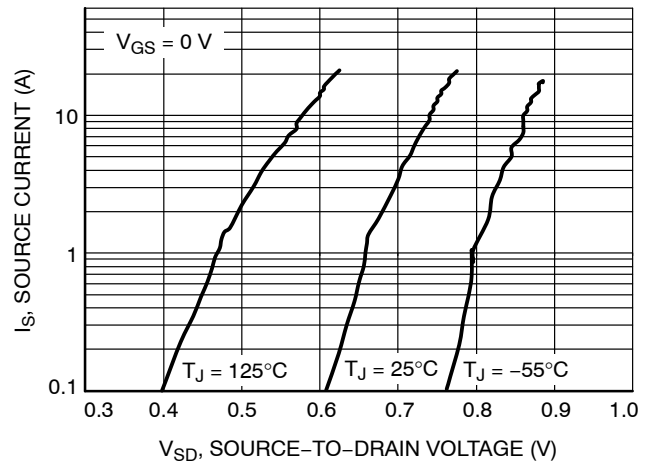


Figure 10. Diode Forward Voltage vs. Current

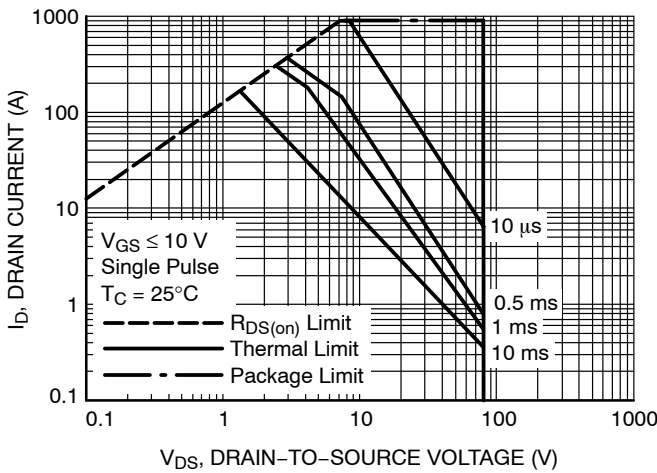


Figure 11. Maximum Rated Forward Biased Safe Operating Area

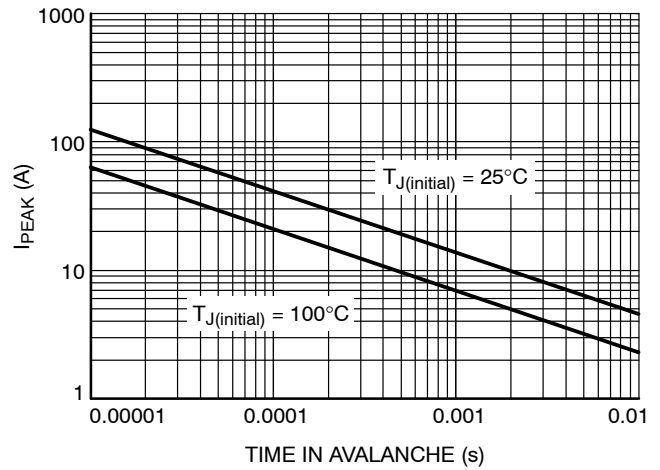


Figure 12. I_{PEAK} vs. Time in Avalanche

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TYPICAL CHARACTERISTICS

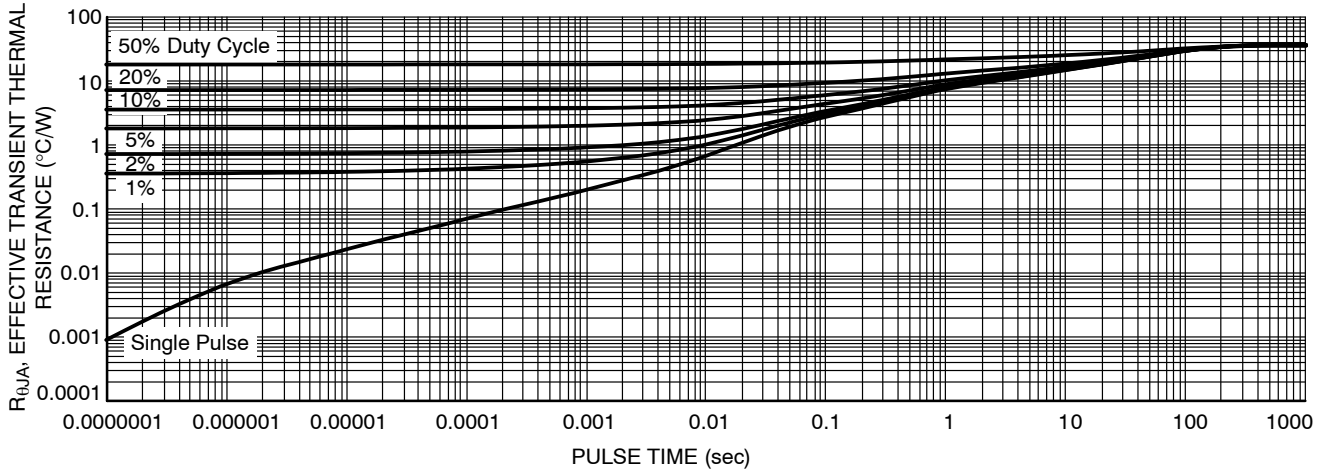


Figure 13. Thermal Response

DEVICE ORDERING INFORMATION

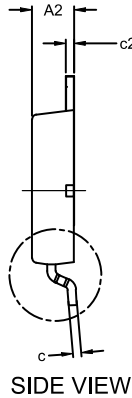
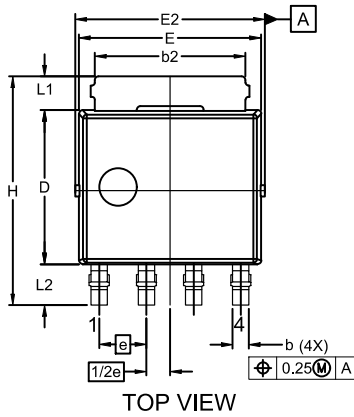
| Device | Marking | Package | Shipping† |
|------------------|----------|---------------------|--------------------|
| NVMYS003N08LHTWG | 003N08LH | LFPAK4 (Pb-Free) | 3000 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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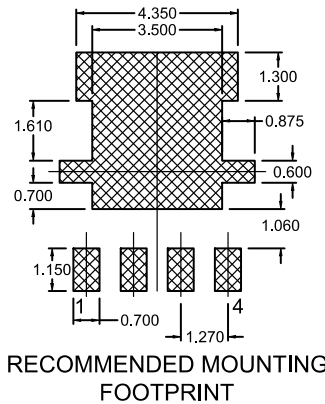
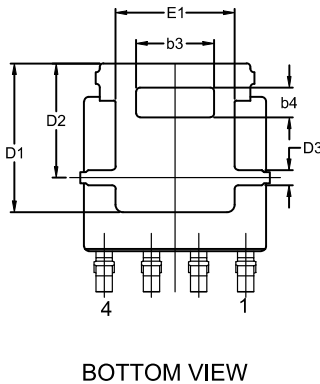
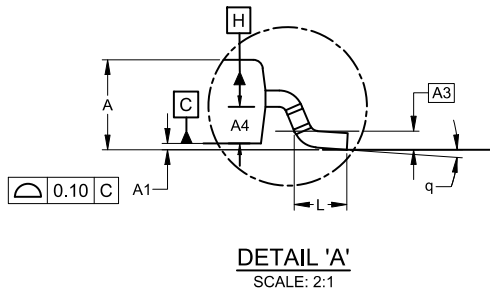
PACKAGE DIMENSIONS

LFPAK4 5x6 CASE 760AB ISSUE A



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.150mm PER SIDE.
4. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.



| UNIT IN MILLIMETER | | | |
|--------------------|----------|------|------|
| DIM | MIN | NOM | MAX |
| A | 1.10 | 1.20 | 1.30 |
| A1 | 0.00 | 0.08 | 0.15 |
| A2 | 1.10 | 1.15 | 1.20 |
| A3 | | 0.25 | |
| A4 | 0.45 | 0.50 | 0.55 |
| b | 0.40 | 0.45 | 0.50 |
| b2 | 3.80 | 4.10 | 4.40 |
| b3 | 2.00 | 2.10 | 2.20 |
| b4 | 0.70 | 0.80 | 0.90 |
| c | 0.19 | 0.22 | 0.25 |
| c2 | 0.19 | 0.22 | 0.25 |
| D | 4.05 | 4.15 | 4.25 |
| D1 | - | - | 4.20 |
| D2 | 3.0 | 3.10 | 3.20 |
| D3 | 0.30 | 0.40 | 0.50 |
| E | 4.80 | 4.90 | 5.00 |
| E1 | 3.10 | 3.20 | 3.30 |
| E2 | 5.00 | 5.15 | 5.30 |
| e | 1.27 BSC | | |
| H | 6.00 | 6.15 | 6.30 |
| L | 0.40 | 0.65 | 0.85 |
| L1 | 0.80 | 0.90 | 1.00 |
| L2 | 0.80 | 1.05 | 1.30 |
| q | 0° | 4° | 8° |

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